

2/9

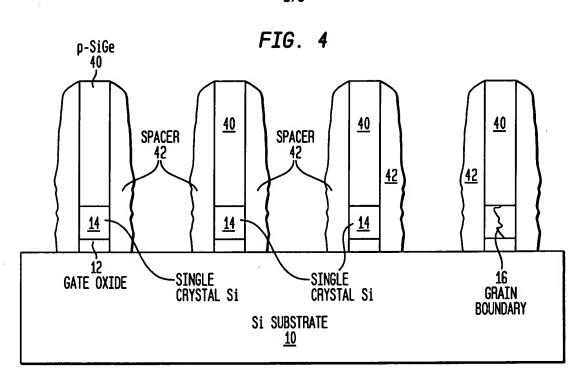
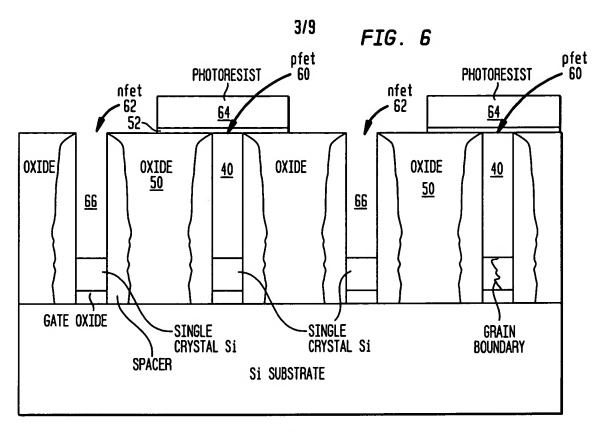
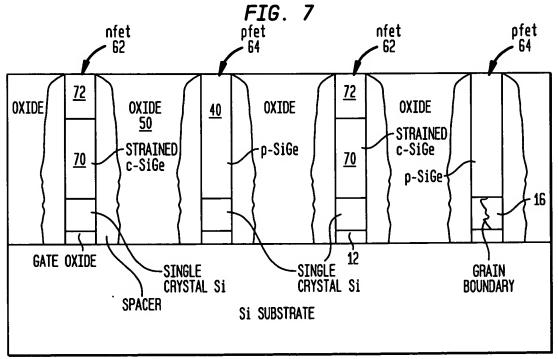
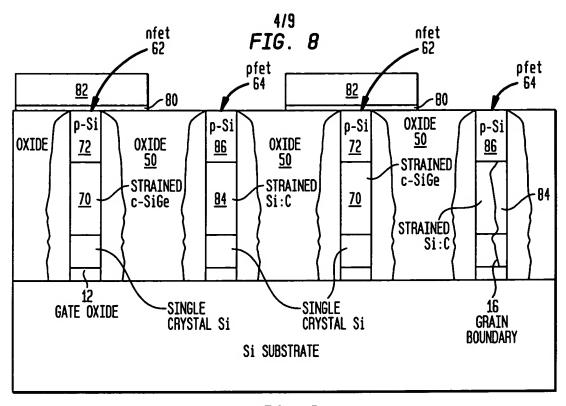
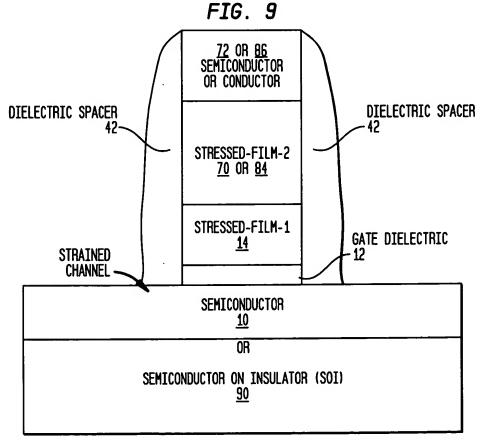


FIG. 5 NITRIDE ·52 0XIDE 50 OXIDE OXIDE OXIDE <u>40</u> <u>40</u> <u>50</u> 14 <u>14</u> <u>14</u> 12 GATE OXIDE GRÁIN BOUNDARY SINGLE CRYSTAL Si SINGLE CRYSTAL Si Si SUBSTRATE

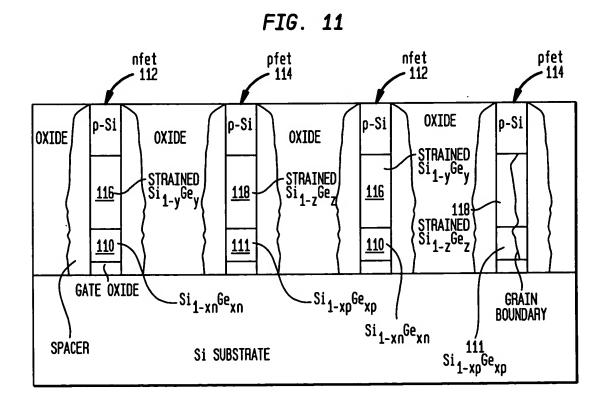








5/9 FIG. 10 pfet - 104 pfet - 104 nfet nfet 102 102 OXIDE p-Si p-Si p-Si p-Si OXIDE OXIDE OXIDE STRAINED Si_{1-y}Ge_y STRAINED Si_{1-y}Ge_y STRAINED Si_{1-z}ge_z STRAINED Si_{1-z}ge_z 108 106 106 OR Si:C OR ·<u>100</u> 100 100 Si:C 100 GRAIN 12 GATE OXIDE Si_{1-x}Ge_x **BOUNDARY** Si_{1-x}Ge_x 42 SPACER Si SUBSTRATE <u>10</u>





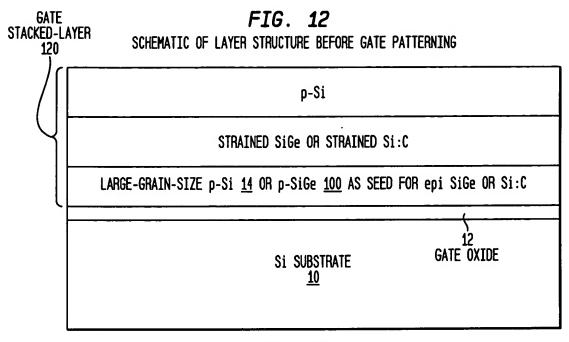


FIG. 13

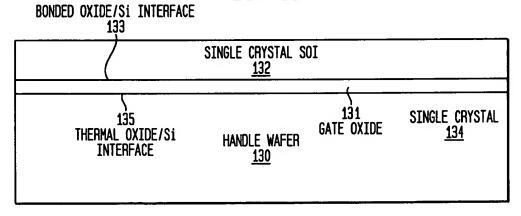


FIG. 14

